Oishi, K., S. Kobayashi and F. Kaneko, Growth and characterization of $CuGaS_2$ thin films on (100) Si by vacuum deposition with three sources 153 (1995) 158
Olchowik, J.M., W. Sadowski and D. Szymczuk, Effect of interface energy on erosion of $A^{III}B^{V}$ substrates during liquid phase heteroepitaxy 153 (1995) 11
Oliver, P.E., see Lane 153 (1995) 25

Pan, Shoukui, Minmin Go and Mingin Chen, Melt growth on MOMONS (3-methoxy-4-methoxy-4'-nitrostilbene) crystals 153 (1995) 55
Ponchet, A., A. Le Corre, A. Godefroy, S. Salaün and A. Poudoulec, Influence of stress and surface reconstruction on the morphology of tensile GaInAs grown on InP(001) by gas source molecular beam epitaxy 153 (1995) 71
Poudoulec, A., see Ponchet 153 (1995) 71

Qin, Z., see Dost 153 (1995) 123
Qin, Z., S. Dost, N. Djilali and B. Tabarrok, A model for liquid phase electroepitaxy under an external magnetic field. II. Application 153 (1995) 131

Regel, L.L., see Shetty 153 (1995) 103
Ritchie, D.M., A. Di Paola, M. Tromby, M. Dellagiovanni,M. Di Egidio and F. Vidimari, Erratum to "Silicon delta-doped AlGaAs by low pressure metalorganic vapor phase epitaxy" 153 (1995) 68
Rolin, T.D. and F.R. Szofran, Determination of the electrical conductivity of liquid $Ge_{0.95}Si_{0.05}$ 153 (1995) 6
Rüfer, H., see Fischer 153 (1995) 90

Sadowski, W., see Olchowik 153 (1995) 11
Saenger, W., see Moré 153 (1995) 35
Saijo, H. and M. Shiojiri, J-aggregates of cyanine dye molecules adsorbed on the surfaces of AgBr emulsion crystals 153 (1995) 31
Salaün, S., see Ponchet 153 (1995) 71
Sant, C. and J.P. Contour, Pulsed laser deposition of $Bi_4Cu_{2x}V_{2(1-x)}O_{11}$ thin films 153 (1995) 63
Saville, D.A., see Grant 153 (1995) 42
Shetty, R. and W.R. Wilcox, Boron nitride coating on fused silica ampoules for semiconductor crystal growth 153 (1995) 97
Shetty, R., W.R. Wilcox and L.L. Regel, Influence of ampoule coatings on cadmium telluride solidification 153 (1995) 103
Shiojiri, M., see Saijo 153 (1995) 31
Smith, N.A., see Lane 153 (1995) 25
Sreeramana Aithal, P. and P. Mohan Rao, Novel nonlinear optical crystal of methyl-p-hydroxy benzoate 153 (1995) 60
Sugiyama, K., see Miyake 153 (1995) 180
Suzuki, T., Defect structure formed in $LiNbO_3$ crystals by reducing undoped $LiNbO_3$ melts 153 (1995) 164
Szofran, F.R., see Rolin 153 (1995) 6
Szymczuk, D., see Olchowik 153 (1995) 11

Tabarrok, B., see Qin 153 (1995) 131
Tilsley, M.E.G., see Lane 153 (1995) 25
Tokutaka, H., see Kishida 153 (1995) 146
Tomzig, E., see Fischer 153 (1995) 90
Tromby, M., see Ritchie 153 (1995) 68

Vidimari, F. , see Ritchie 153 (1995) 68

Wang, C.A., see Krueger 153 (1995) 81
Wang, G., H.G. Gallagher, T.P.J. Han and B. Henderson, Crystal growth and optical characterisation of Cr^{3+}-doped $YAl_3(BO_3)_4$ 153 (1995) 169
Watanabe, N., see Yoshida 153 (1995) 151
Wen, J.G., see Yoshida 153 (1995) 151
Wilcox, W.R., see Shetty 153 (1995) 97
Wilcox, W.R., see Shetty 153 (1995) 103
Wright, P.J., see Lane 153 (1995) 25

Yamada, M., see Miyake 153 (1995) 180
Yoshida, Y., J.G. Wen, N. Watanabe, N. Koshizuka and T. Morishita, Preparation of $YBa_2Cu_4O_8$ thin films from precursors deposited by hybrid plasma sputtering through in situ annealing 153 (1995) 151
Yumoto, T., see Kishida 153 (1995) 146

Zhou, J.M., see Guo 153 (1995) 110

ELSEVIER

Journal of Crystal Growth 153 (1995) 186–187

JOURNAL OF CRYSTAL GROWTH

Subject index

Apparatus
– for melt growth
– – by Bridgman–Stockbarger method
– – – of semiconductors with BN coated ampoules 97
– for solution growth
– – by crystallization in microgravity
– – – of proteins 175
– for miscellaneous purposes
– – electrical conductivity measurement of liquid germanium silicon 6

Cadmium
– telluride 103
Characterization
– by AFM
– – of spiral growth mechanism 63
– by MAKYOH topography
– – of indium phosphide 1
Computer simulation
– of liquid phase electroepitaxy 131
– of liquid phase heteroepitaxy 11
– of misfit dislocation and critical thickness of zinc blende crystals 115
Convection 19, 42, 123, 131
Copper
– aluminum disulphide 180
– gallium disulphide 158, 180

Epitaxy, see Thin film growth

Gallium
– indium arsenide 71
Germanium
– silicon 6, 110

Hydrodynamics, see Convection

Indium
– phosphide 1, 71

Kinetics
– of etching of gallium arsenide by CI 81
– of growth 19, 25, 35, 42, 110, 140, 169
– of interface control 71

Lasers, crystals for
– methyl-p-hydroxy benzoate 60
– chromium doped yttrium aluminum borate 169

Manganese
– arsenide antimonide 25
Melt growth technique
– by Bridgman–Stockbarger method
– – of MOMONS (3-methoxy-4-methoxy-4′-nitrostilbene) 55
– – of cadmium telluride 103
– by Czochralski method
– – of gallium arsenide 90
– – of lithium niobate 164
– by liquid phase electroepitaxy
– – theory of 19
Microgravity, growth under
– of semiconductors 97
– of cadmium telluride 103
– of human protein 175
Morphological stability
– of gallium arsenide surfaces 81

Nucleation
– of DCBO 140

Phase diagram
– of YBCO 151
Precursor
– for YBCO 151

Silicon
– germanium 6, 110
Solution growth technique
– by gel method
– – of methyl-p-hydroxy benzoate 60
– by flux method
– – of BSCCO 146
– – of yttrium aluminum borate 169
– by slotting out
– – of concanavalin A crystals 35
Superconductivity materials, high T_c
– bulk
– – of BSCCO 146
– film

– – of DBCO 140
– – of YBCO 151
Superlattices, multilayers
– of III–V compounds 71
Surface energy, determination
– of interface energy 11
Surface morphology
– of indium phosphide 1
– of YBCO 151
Surface structure
– of protein crystals 35
– of gallium indium arsenide 71
– of etched gallium arsenide 81
– of heteroepitaxy 115

Thin film growth, epitaxy
– by atomic layer molecular beam epitaxy
– – theory of 140
– by hybrid plasma sputtering
– – of YBCO 151
– by liquid phase epitaxy
– – of III-V compounds 11
– – of cyamine dye molecules 31
– by liquid phase electroepitaxy
– – of gallium arsenide 131
– – theory of 123
– – of gallium indium arsenide 71
– – of indium phosphide 71
– – of silicon germanium 110
– – theory of 140
– by pulsed laser deposition
– – of bismuth copper vanadium oxide 63
– by vapor phase epitaxy
– – through chemical vapor deposition
– – – of copper aluminum disulphide 180
– – – of copper gallium disulphide 180
– – through evaporation and condensation
– – – of manganese antimonide 25
– – – of manganese arsenide antimonide 25

Vapor growth technique
– by evaporation and condensation
– – of copper gallium disulphide 158
– by vapor diffusion 175